



# 《风光欣》技术资料

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## S8550 (ECB) PNP EPITAXIAL SILICON TRANSISTOR

1W OUTPUT AMPLIFIER OF PORTABLE  
RADIOS IN CLASS

B PUSH-PULL OPERATION

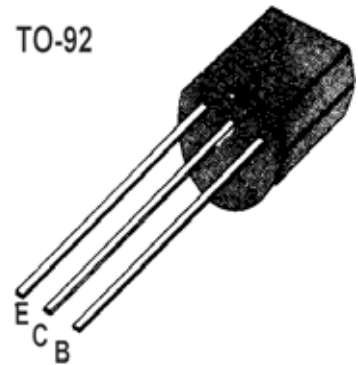
\* Complimentary to S8050

\* Collector Current  $I_{cm} = 0.8A$

\* Collector Dissipation:  $P_c = 0.8W (T_c = 25)$

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-25	V
Emitter -Base Voltage	$V_{EB0}$	-6	V
Collector Current	$I_c$	-0.8	A
Collector Dissipation	$P_c$	0.8	W
Junction Temperature	$T_j$	150	
Storage Temperature	$T_{STG}$	-65 ~150	



### ELECTRICAL CHARACTERISTICS ( $T_A = 25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CB0}$	$I_c = -100 \mu A, I_E = 0$	-40			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_c = -2mA, I_B = 0$	-25			V
Emitter-Base Breakdown Voltage	$BV_{EB0}$	$I_E = -100 \mu A, I_c = 0$	-6			V
Collector Cut-off Current	$I_{CB0}$	$V_{CB} = -35V, I_E = 0$			-100	nA
Emitter Cut-off Current	$I_{EB0}$	$V_{EB} = -6V, I_c = 0$			-100	nA
DC Current Gain	HFE1	$V_{CE} = -1V, I_c = -5mA$	45	170		
	HFE2	$V_{CE} = -1V, I_c = -500mA$	85	160	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.28	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = -500mA, I_B = -50mA$		-0.98	-1.2	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -1V, I_c = -10mA$		-0.66	-1.0	V
Output Capacitance	$C_{OB F=1MHz}$	$V_{CB} = -10V, I_E = 0$		15		pF
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = -10V, I_c = -50mA$	100	200		MHz

### HFE(2) CLASSIFICATIC

Classification	B	C	D	E	F
HFE(2)	85-160	120-200	160-300	300-400	400-500